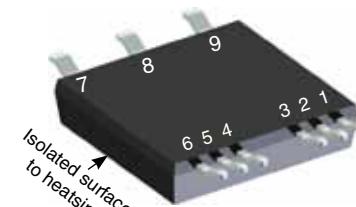
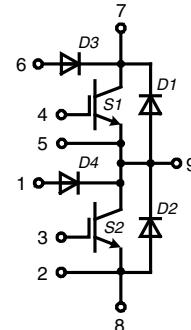


# XPT IGBT phaseleg

## ISOPLUS™

### Surface Mount Power Device

**I<sub>C25</sub>** = 32 A  
**V<sub>CES</sub>** = 1200 V  
**V<sub>CE(sat)</sub> typ** = 1.8 V



E72873

**IGBTs S1, S2**

Symbol	Conditions	Maximum Ratings		
V <sub>CES</sub>	T <sub>VJ</sub> = 25°C to 150°C	1200	V	
V <sub>GES</sub>		±20	V	
I <sub>C25</sub>	T <sub>C</sub> = 25°C	32	A	
I <sub>C80</sub>	T <sub>C</sub> = 80°C	23	A	
I <sub>CM</sub>	V <sub>GE</sub> = 15 V; R <sub>G</sub> = 56 Ω; T <sub>VJ</sub> = 125°C	45	A	
V <sub>CEK</sub>	RBSOA, clamped inductive load; L = 100 μH	V <sub>CES</sub>		
t <sub>sc</sub> (SCSOA)	V <sub>CE</sub> = 900 V; V <sub>GE</sub> = ±15 V; R <sub>G</sub> = 56 Ω; T <sub>VJ</sub> = 125°C none repetitive	10	μs	
P <sub>tot</sub>	T <sub>C</sub> = 25°C	130	W	

**Symbol**    **Conditions****Characteristic Values**(T<sub>VJ</sub> = 25°C, unless otherwise specified)

		min.	typ.	max.	
V <sub>CE(sat)</sub>	I <sub>C</sub> = 15 A; V <sub>GE</sub> = 15 V; T <sub>VJ</sub> = 25°C T <sub>VJ</sub> = 125°C		1.8 2.1	2.1	V
V <sub>GE(th)</sub>	I <sub>C</sub> = 0.6 mA; V <sub>GE</sub> = V <sub>CE</sub>	5.4		6.5	V
I <sub>CES</sub>	V <sub>CE</sub> = V <sub>CES</sub> ; V <sub>GE</sub> = 0 V; T <sub>VJ</sub> = 25°C T <sub>VJ</sub> = 125°C		250	125	μA
I <sub>GES</sub>	V <sub>CE</sub> = 0 V; V <sub>GE</sub> = ± 20 V			500	nA
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> E <sub>on</sub> E <sub>off</sub> E <sub>(rec)off</sub>	Inductive load; T <sub>VJ</sub> = 125°C V <sub>CE</sub> = 600 V; I <sub>C</sub> = 15 A V <sub>GE</sub> = ±15 V; R <sub>G</sub> = 56 Ω		70 40 250 100 1.55 1.7		ns ns ns ns mJ mJ
C <sub>ies</sub> Q <sub>Gon</sub>	V <sub>CE</sub> = 25 V; V <sub>GE</sub> = 0 V; f = 1 MHz V <sub>CE</sub> = 600 V; V <sub>GE</sub> = 15 V; I <sub>C</sub> = 15 A		tbd 48		pF nC
R <sub>thJC</sub> R <sub>thJH</sub>	with heatsink compound (IXYS test setup)		1.35	1.0 1.7	K/W K/W

**Features****• XPT IGBT**

- low saturation voltage
- positive temperature coefficient for easy paralleling
- fast switching
- short tail current for optimized performance in resonant circuits

**• Sonic™ diode**

- fast reverse recovery
- low operating forward voltage
- low leakage current

**• V<sub>CEsat</sub> detection diode**

- integrated into package
- very fast diode

**• Package**

- isolated back surface
- low coupling capacity between pins and heatsink
- PCB space saving
- enlarged creepage towards heatsink
- application friendly pinout
- low inductive current path
- high reliability

**Applications****• Phaseleg**

- buck-boost chopper

**• Full bridge**

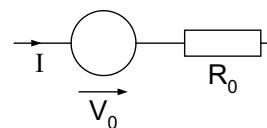
- power supplies
- induction heating
- four quadrant DC drives
- controlled rectifier

**• Three phase bridge**

- AC drives
- controlled rectifier

**Diodes D1, D2**

Symbol	Conditions	Maximum Ratings		
I <sub>F25</sub>	T <sub>C</sub> = 25°C		27	A
I <sub>F80</sub>	T <sub>C</sub> = 80°C		18	A
Symbol	Conditions	Characteristic Values		
		(T <sub>VJ</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
V <sub>F</sub>	I <sub>F</sub> = 20 A	T <sub>VJ</sub> = 25°C	2.0	2.3
		T <sub>VJ</sub> = 125°C	2.0	V
I <sub>RM</sub> t <sub>rr</sub> E <sub>rec</sub>	I <sub>F</sub> = 20 A; R <sub>G</sub> = 56 Ω; T <sub>VJ</sub> = 125°C V <sub>R</sub> = 600 V; V <sub>GE</sub> = -15 V		20 350 tbd	A ns mJ
R <sub>thJC</sub>	per diode		1.35	K/W
R <sub>thJH</sub>	with heatsink compound (IXYS test setup)		1.75	K/W

**Equivalent Circuits for Simulation****Conduction**

IGBTs (typ. at V<sub>GE</sub> = 15 V; T<sub>J</sub> = 125°C)  
S1, S2 V<sub>o</sub> = 1.1 V; R<sub>o</sub> = 90 mΩ

Diodes (typ. at T<sub>J</sub> = 125°C)  
D1, D2 V<sub>o</sub> = 1.3 V; R<sub>o</sub> = 41 mΩ

**Diodes D3, D4**

Symbol	Conditions	Maximum Ratings		
V <sub>R</sub>	T <sub>C</sub> = 25°C to 150°C		1200	V
Symbol	Conditions	Characteristic Values		
		(T <sub>VJ</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
V <sub>F</sub>	I <sub>F</sub> = 1 A	T <sub>VJ</sub> = 25°C	1.7	2.2
		T <sub>VJ</sub> = 125°C	1.5	V
I <sub>R</sub>	V <sub>R</sub> = 1200 V	T <sub>VJ</sub> = 25°C		2
		T <sub>VJ</sub> = 125°C	30	μA
I <sub>RM</sub> t <sub>rr</sub>	I <sub>F</sub> = 1 A; di <sub>F</sub> /dt = -100 A/μs; T <sub>VJ</sub> = 25°C V <sub>R</sub> = 100 V; V <sub>GE</sub> = 0 V		2.3 40	A ns

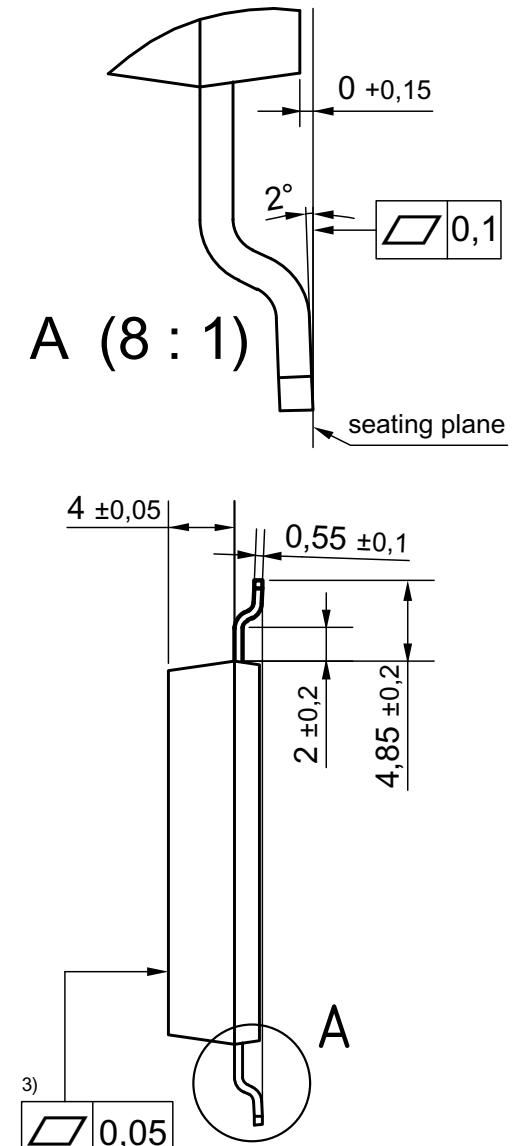
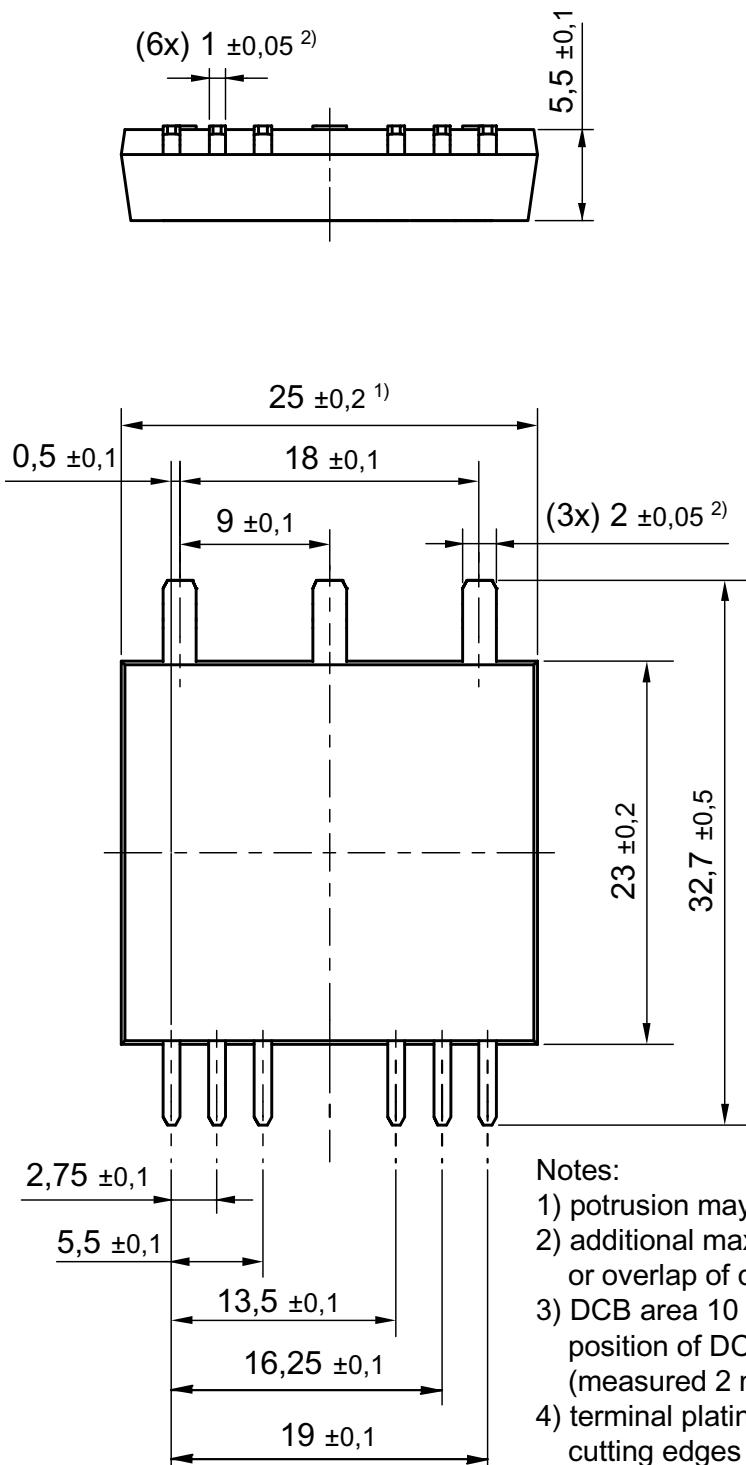
**Component**

Symbol	Conditions	Maximum Ratings		
T <sub>VJ</sub>		-55...+150	°C	
T <sub>stg</sub>		-55...+125	°C	
V <sub>ISOL</sub>	I <sub>ISOL</sub> ≤ 1 mA; 50/60 Hz	2500	V~	
F <sub>c</sub>	mounting force	40 ... 130	N	

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C <sub>P</sub>	coupling capacity between shorted pins and backside metal		90	pF
d <sub>S</sub> , d <sub>A</sub>	pin - pin	1.65		mm
d <sub>S</sub> , d <sub>A</sub>	pin - backside metal	4		mm
CTI		400		
Weight			8	g

Ordering	Ordering Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	IXA20PG1200DHGLB	IXA20PG1200DHGLB	Tape&Reel	200	tbd

Dimensions in mm (1 mm = 0.0394")



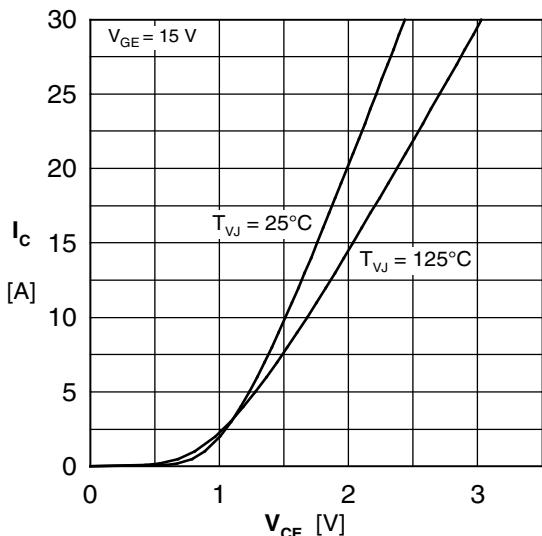


Fig. 1 Typ. output characteristics

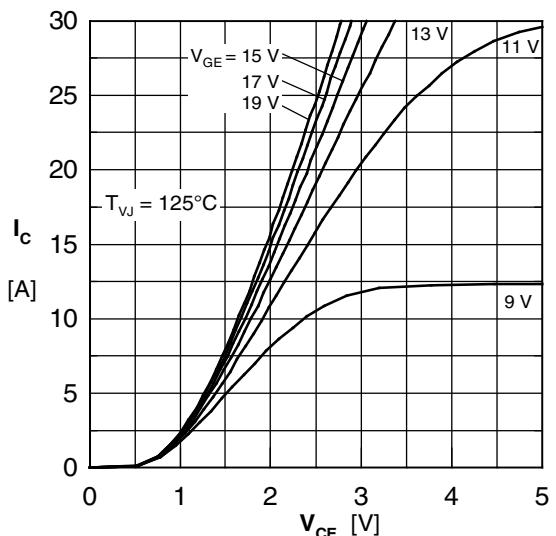


Fig. 2 Typ. output characteristics

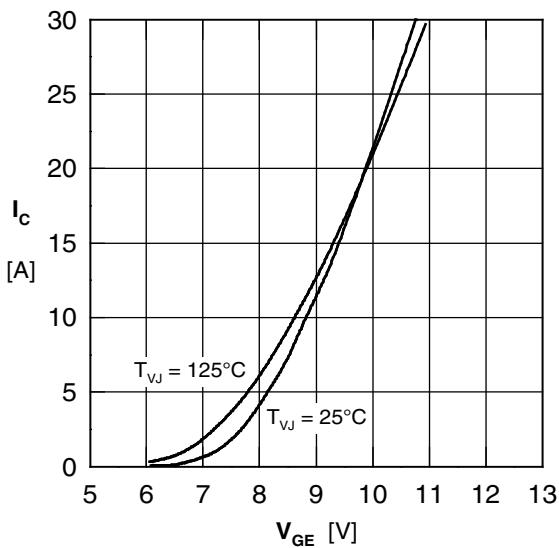


Fig. 3 Typ. tranfer characteristics

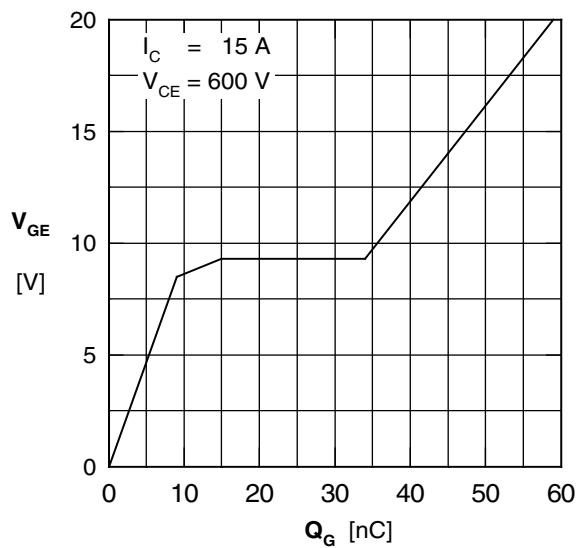


Fig. 4 Typ. turn-on gate charge

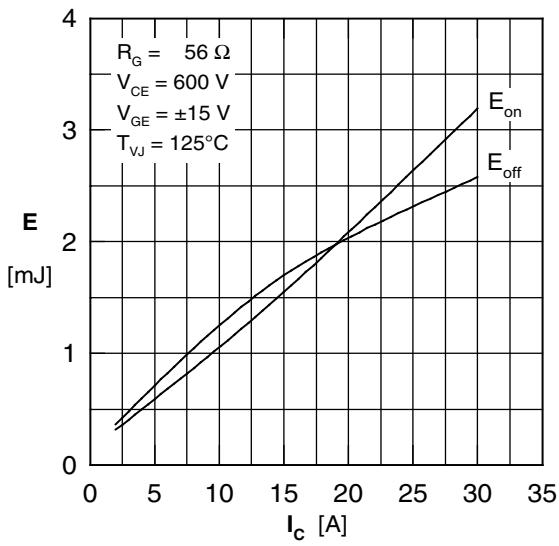


Fig. 5 Typ. switching energy vs. collector current

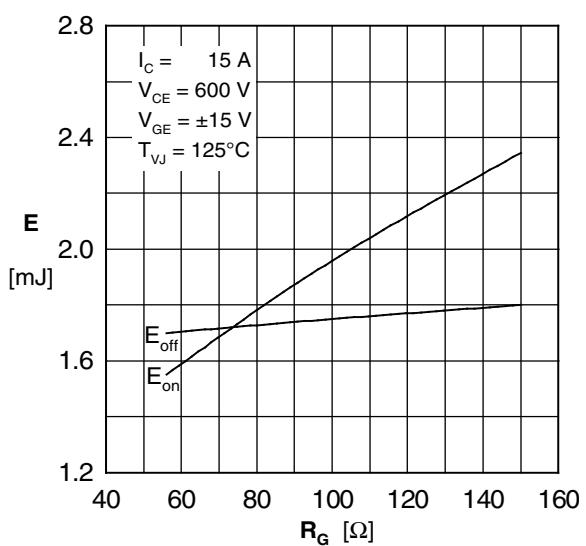


Fig. 6 Typ. switching energy vs. gate resistance

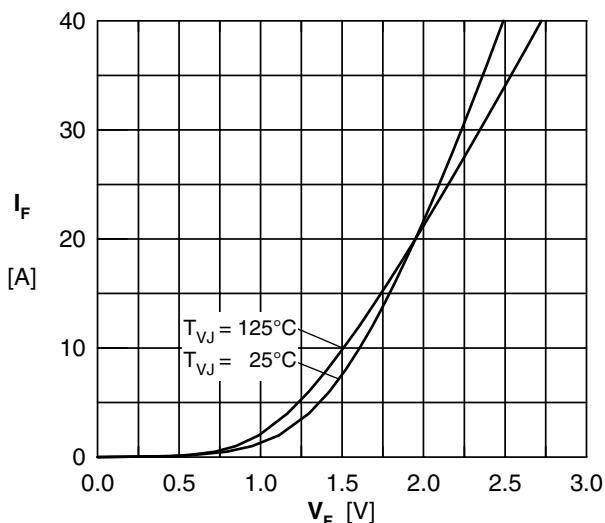
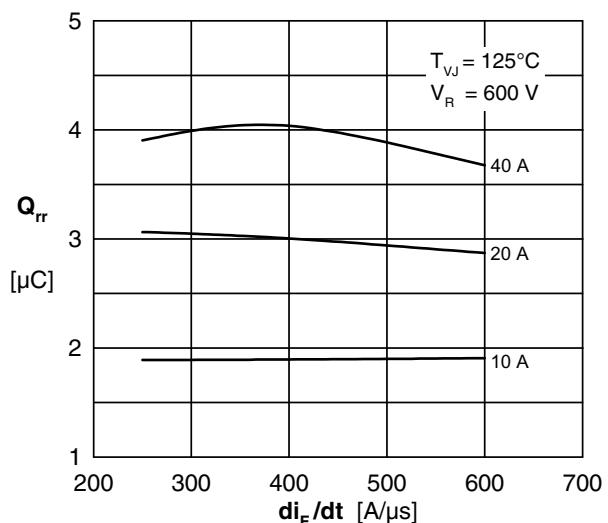
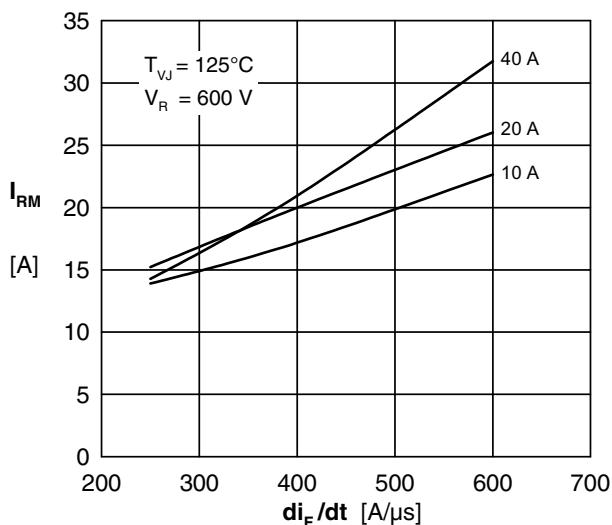
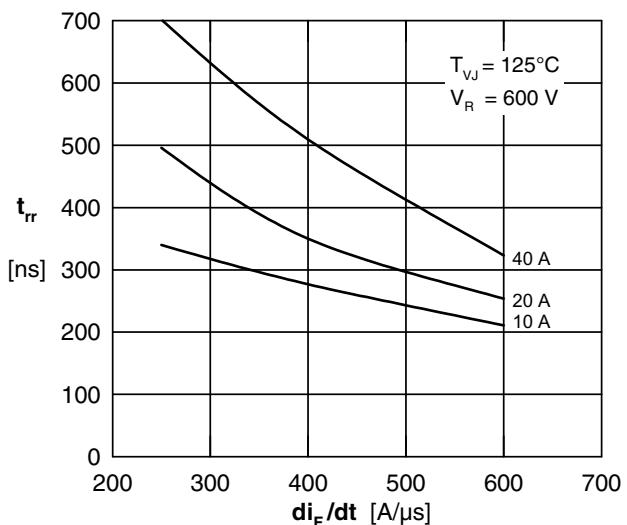
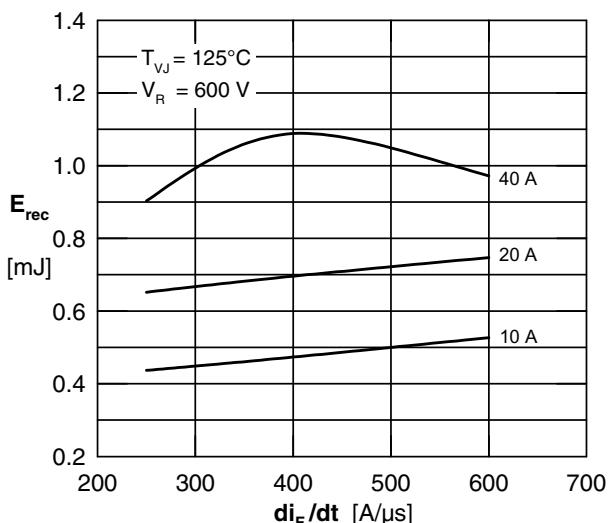
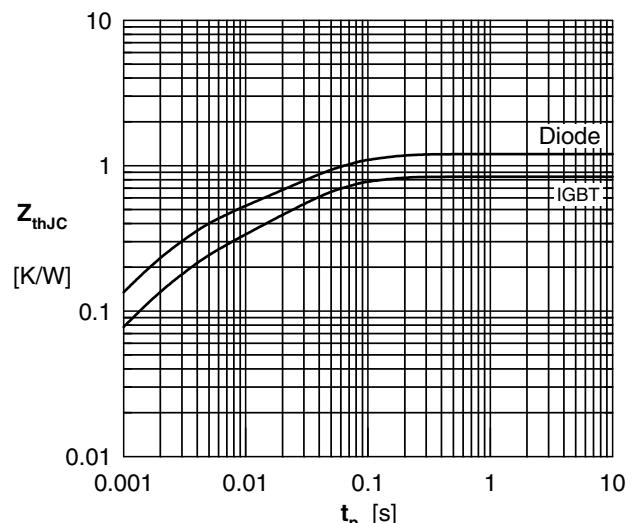
Fig. 7 Typ. Forward current versus  $V_F$ Fig. 8 Typ. reverse recov.charge  $Q_{rr}$  vs.  $\text{di}/\text{dt}$ Fig. 9 Typ. peak reverse current  $I_{RM}$  vs.  $\text{di}/\text{dt}$ Fig. 10 Typ. recovery time  $t_{rr}$  versus  $\text{di}/\text{dt}$ Fig. 11 Typ. recovery energy  $E_{rec}$  versus  $\text{di}/\text{dt}$ 

Fig. 12 Typ. transient thermal impedance



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